

EconoDUAL™3 module with TRENCHSTOP™ IGBT7 and Emitter Controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{nom}} = 600\text{ A} / I_{CRM} = 1200\text{ A}$
 - Integrated temperature sensor
 - TRENCHSTOP™ IGBT7
 - V_{CESat} with positive temperature coefficient
- Mechanical features
 - High power density
 - Isolated base plate
 - PressFIT contact technology
 - Standard housing



Typical appearance

Potential applications

- Commercial Agriculture Vehicles
- High power converters
- Motor drives
- Servo drives
- UPS systems

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

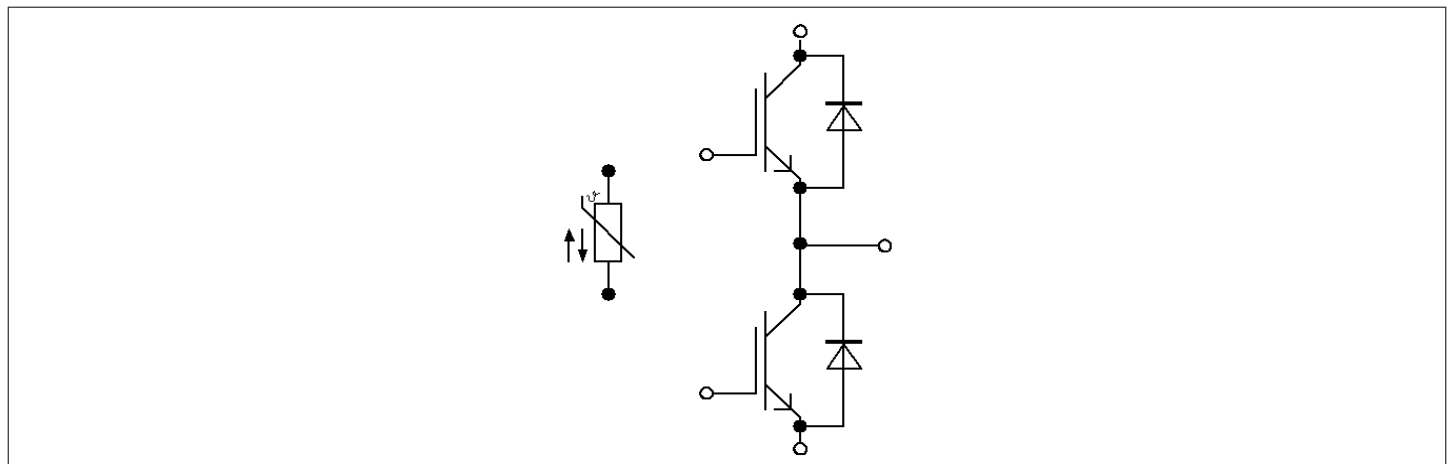


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	3.4	kV
Material of module baseplate			Cu	
Internal Isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	14.5	mm
Creepage distance	d_{Creep}	terminal to terminal	13.0	mm
Clearance	d_{Clear}	terminal to heatsink	12.5	mm
Clearance	d_{Clear}	terminal to terminal	10.0	mm
Comparative tracking index	CTI		> 200	
RTI Elec.	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Stray inductance module	L_{SCE}			20		nH	
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		0.8		mΩ	
Storage temperature	T_{stg}		-40		125	°C	
Mounting torque for modul mounting	M	- Mounting according to valid application note	M5, Screw	3		6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M6, Screw	3		6	Nm
Weight	G			345		g	

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 85^\circ\text{C}$	600	A
Repetitive peak collector current	I_{CRM}	$t_p = 1 \text{ ms}$	1200	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 600\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.50	1.75	V
			$T_{vj} = 125\ ^\circ C$		1.65		
			$T_{vj} = 175\ ^\circ C$		1.75		
Gate threshold voltage	V_{GEth}	$I_C = 12\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.15	5.80	6.45	V	
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$		9.6		μC	
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0.56		Ω	
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		92		nF	
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		0.46		nF	
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			35	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 600\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.51\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.250		μs	
			$T_{vj} = 125\ ^\circ C$	0.270			
			$T_{vj} = 175\ ^\circ C$	0.290			
Rise time (inductive load)	t_r	$I_C = 600\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.51\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.065		μs	
			$T_{vj} = 125\ ^\circ C$	0.072			
			$T_{vj} = 175\ ^\circ C$	0.074			
Turn-off delay time (inductive load)	t_{doff}	$I_C = 600\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 0.51\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.420		μs	
			$T_{vj} = 125\ ^\circ C$	0.500			
			$T_{vj} = 175\ ^\circ C$	0.540			
Fall time (inductive load)	t_f	$I_C = 600\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 0.51\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.125		μs	
			$T_{vj} = 125\ ^\circ C$	0.270			
			$T_{vj} = 175\ ^\circ C$	0.370			
Turn-on energy loss per pulse	E_{on}	$I_C = 600\ A, V_{CE} = 600\ V, L_\sigma = 25\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 0.51\ \Omega, di/dt = 7800\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	24		mJ	
			$T_{vj} = 125\ ^\circ C$	43			
			$T_{vj} = 175\ ^\circ C$	58			
Turn-off energy loss per pulse	E_{off}	$I_C = 600\ A, V_{CE} = 600\ V, L_\sigma = 25\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 0.51\ \Omega, dv/dt = 3100\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	50.5		mJ	
			$T_{vj} = 125\ ^\circ C$	77			
			$T_{vj} = 175\ ^\circ C$	95.5			
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_P \leq 8\ \mu s, T_{vj} \leq 150\ ^\circ C$	2500		A	
			$t_P \leq 6\ \mu s, T_{vj} \leq 175\ ^\circ C$	2400			

Table 4 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.0721	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}^2\text{K})$		0.0193		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25^\circ\text{C}$	1200	V	
Continuous DC forward current	I_F		600	A	
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$	1200	A	
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	28300	A^2s
			$T_{vj} = 175^\circ\text{C}$	26000	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 600 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.80	2.10	V
			$T_{vj} = 125^\circ\text{C}$		1.70		
			$T_{vj} = 175^\circ\text{C}$		1.60		
Peak reverse recovery current	I_{RM}	$V_R = 600 \text{ V}, I_F = 600 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 7800 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		400		A
			$T_{vj} = 125^\circ\text{C}$		550		
			$T_{vj} = 175^\circ\text{C}$		625		
Recovered charge	Q_r	$V_R = 600 \text{ V}, I_F = 600 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 7800 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		38		μC
			$T_{vj} = 125^\circ\text{C}$		79.5		
			$T_{vj} = 175^\circ\text{C}$		108		

Table 6 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	$V_R = 600\text{ V}$, $I_F = 600\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 7800\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	19		mJ
			$T_{vj} = 125\text{ °C}$	39		
			$T_{vj} = 175\text{ °C}$	53		
Thermal resistance, junction to case	R_{thJC}	per diode			0.141	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m} \cdot \text{K})$		0.0230		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 NTC-Thermistor

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}$, $R_{100} = 493\text{ }\Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

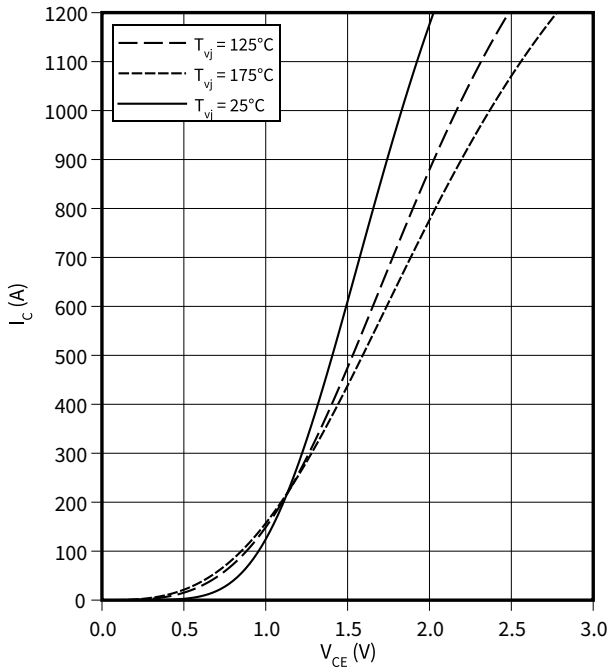
Note: Specification according to the valid application note.

5 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

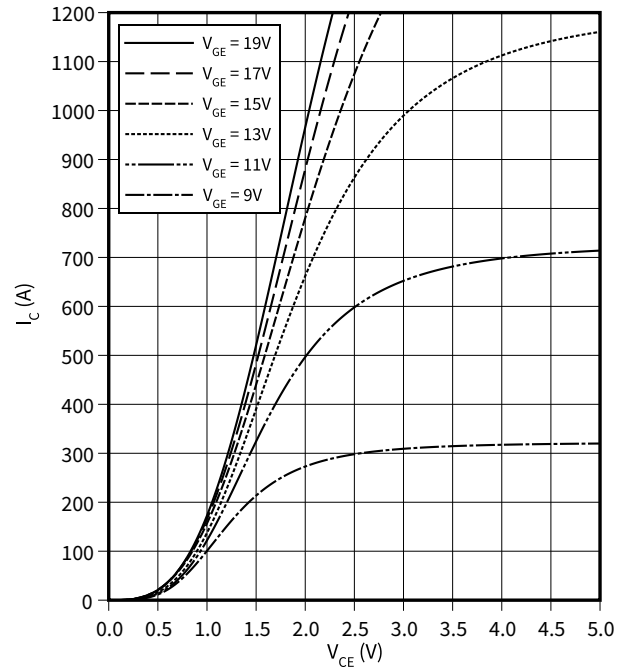
$$V_{GE} = 15 \text{ V}$$



output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

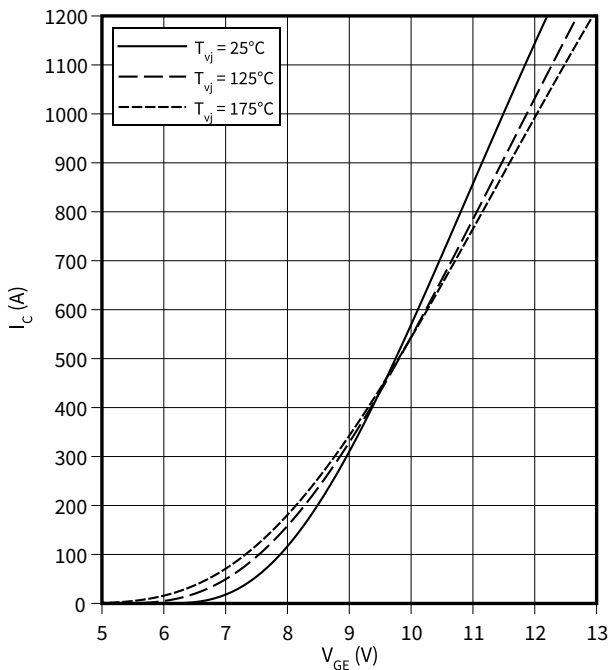
$$T_{vj} = 175 \text{ °C}$$



transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

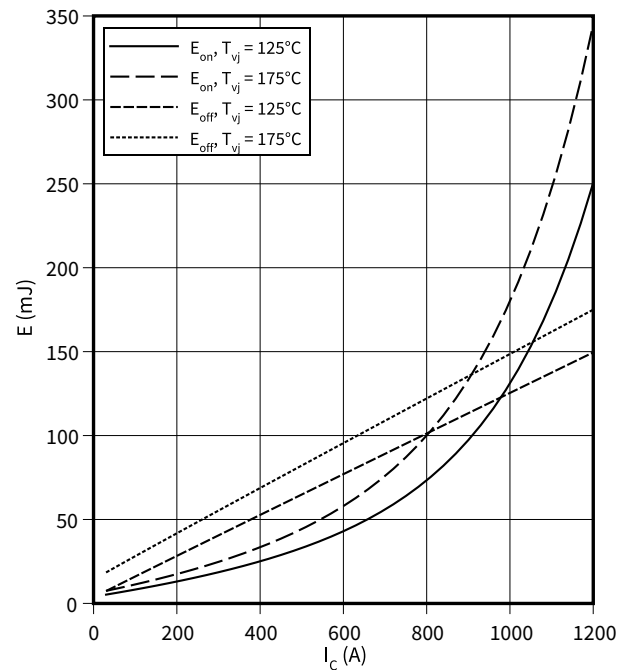
$$V_{CE} = 20 \text{ V}$$



switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

$$R_{Goff} = 0.51 \text{ } \Omega, R_{Gon} = 0.51 \text{ } \Omega, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$$

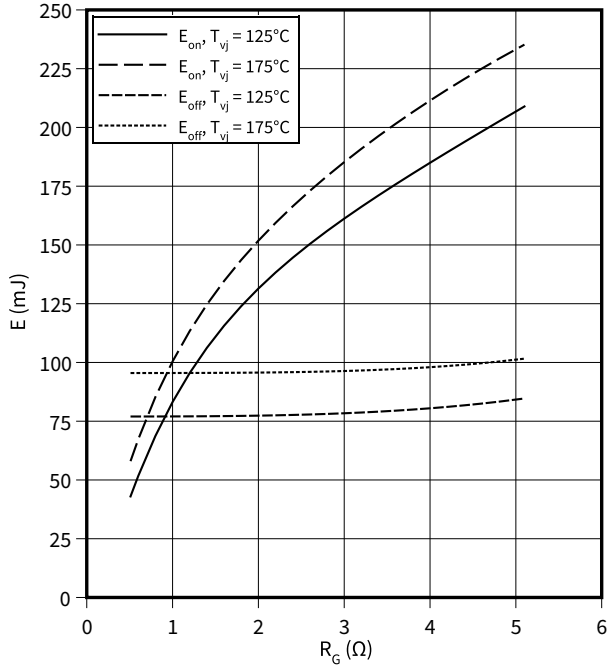


5 Characteristics diagrams

switching losses (typical), IGBT, Inverter

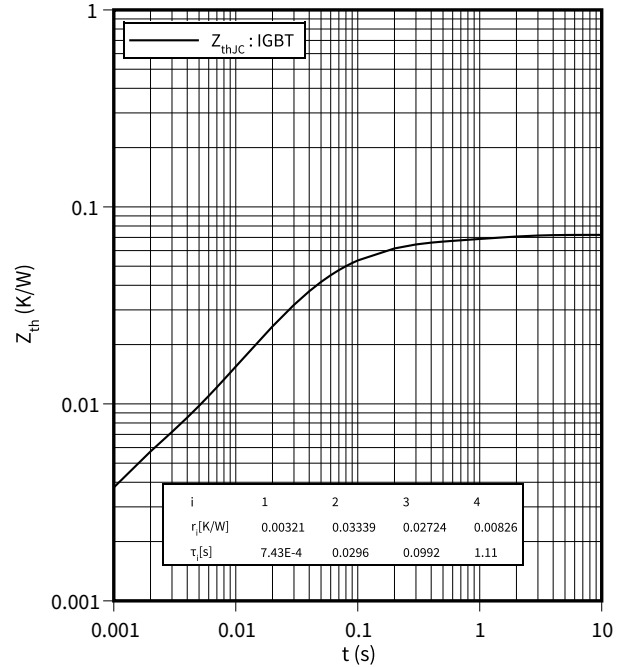
$E = f(R_G)$

$I_C = 600 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$



transient thermal impedance, IGBT, Inverter

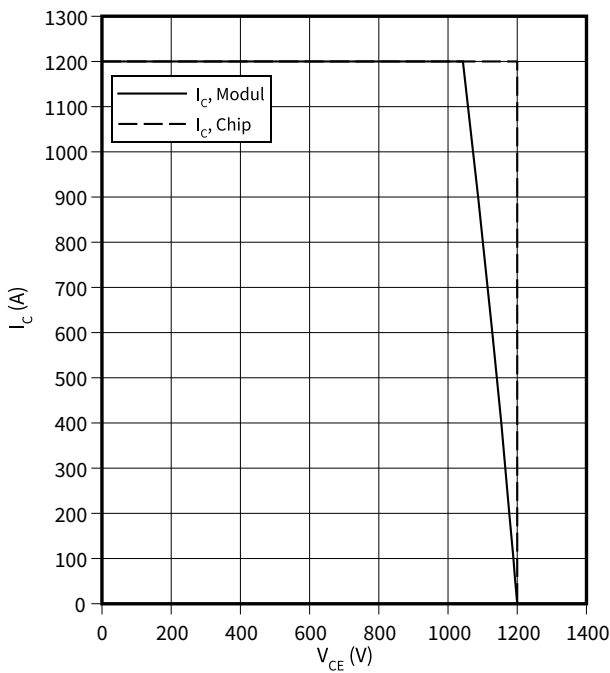
$Z_{th} = f(t)$



reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

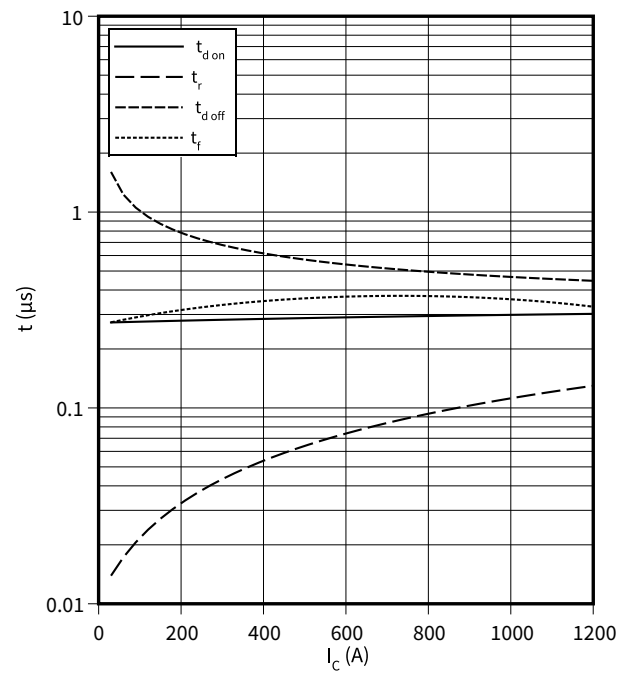
$R_{Goff} = 0.51 \Omega, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ °C}$



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

$R_{Goff} = 0.51 \Omega, R_{Gon} = 0.51 \Omega, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ °C}$

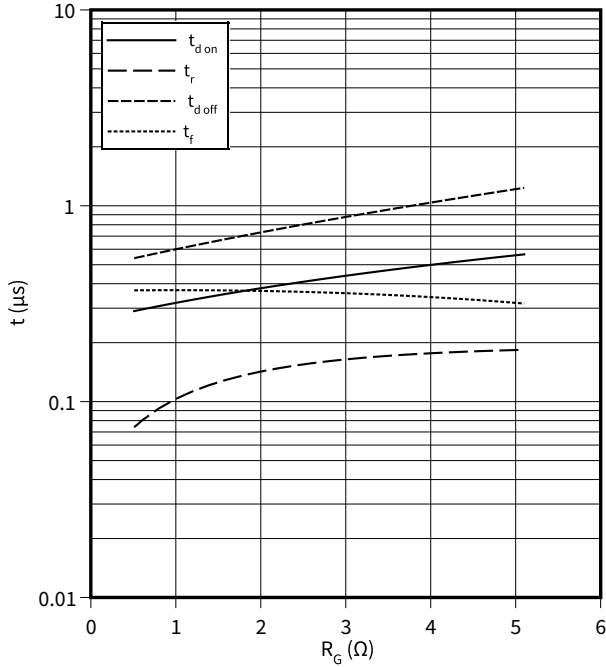


5 Characteristics diagrams

Switching times (typical), IGBT, Inverter

$t = f(R_G)$

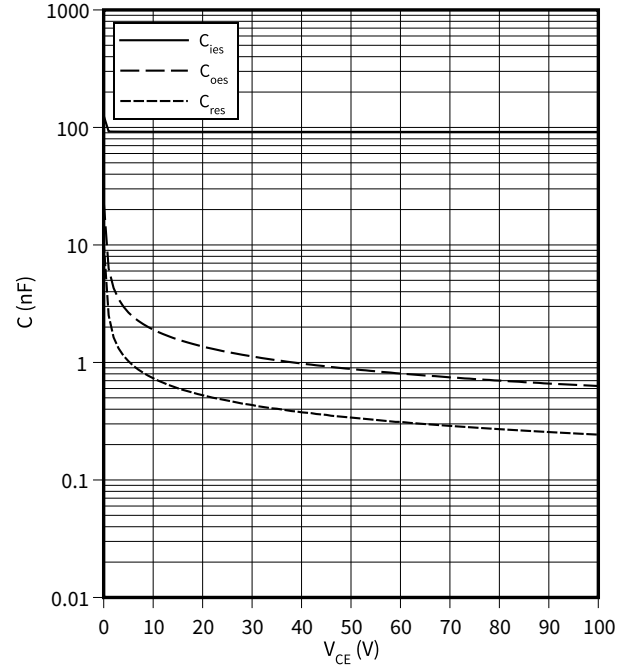
$I_C = 600 \text{ A}$, $V_{CE} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ }^\circ\text{C}$



capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

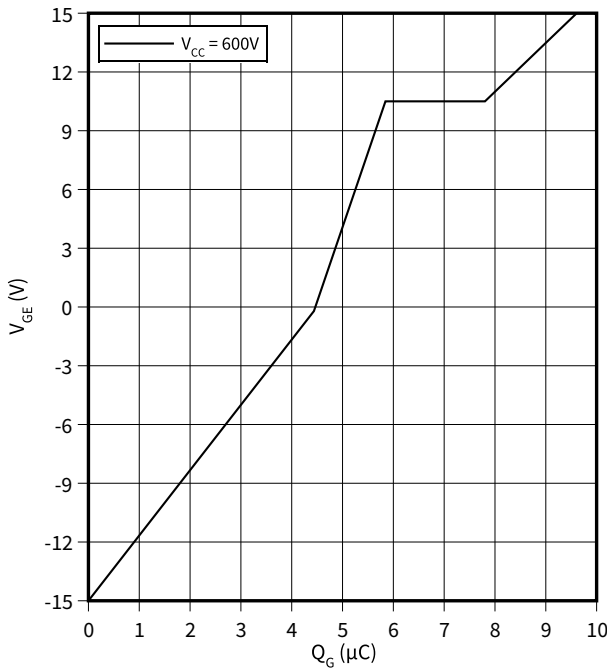
$f = 100 \text{ kHz}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



gate charge characteristic (typical), IGBT, Inverter

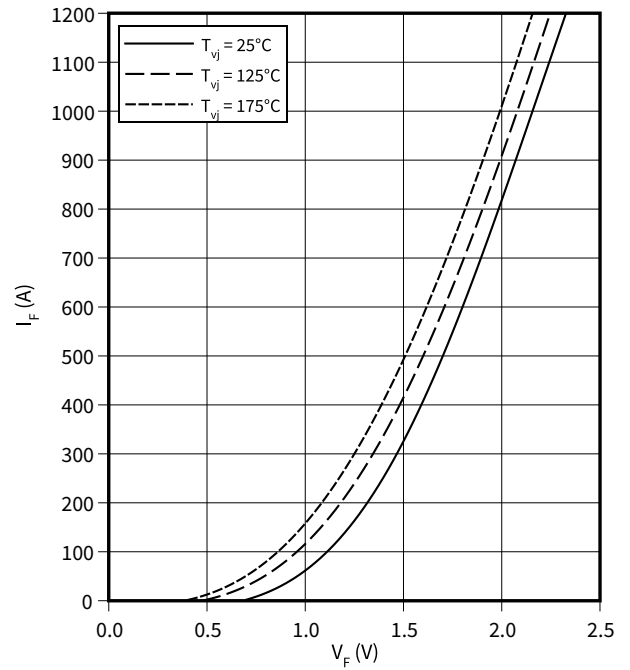
$V_{GE} = f(Q_G)$

$I_C = 600 \text{ A}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



forward characteristic of (typical), Diode, Inverter

$I_F = f(V_F)$

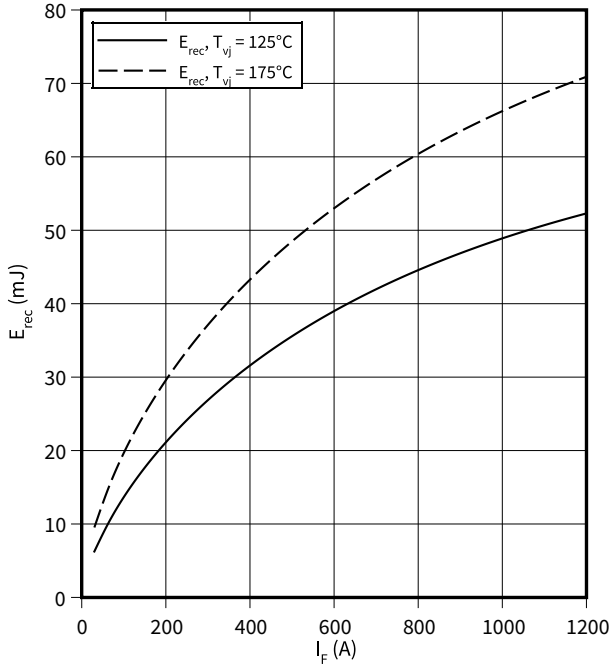


5 Characteristics diagrams

switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

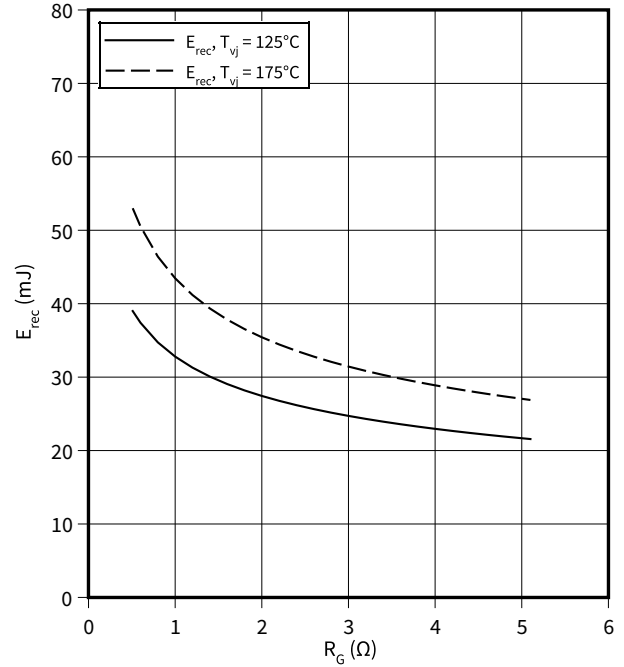
$V_{CE} = 600\text{ V}, R_{Gon} = R_{Gon}(IGBT)$



switching losses (typical), Diode, Inverter

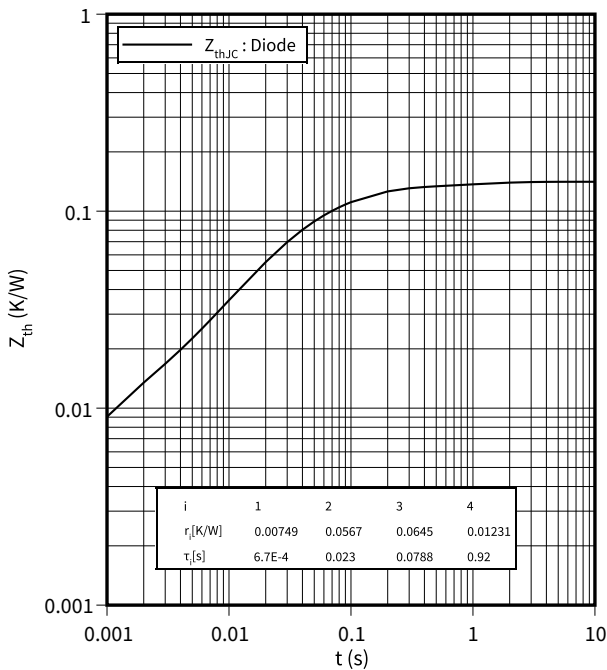
$E_{rec} = f(R_G)$

$V_{CE} = 600\text{ V}, I_F = 600\text{ A}$



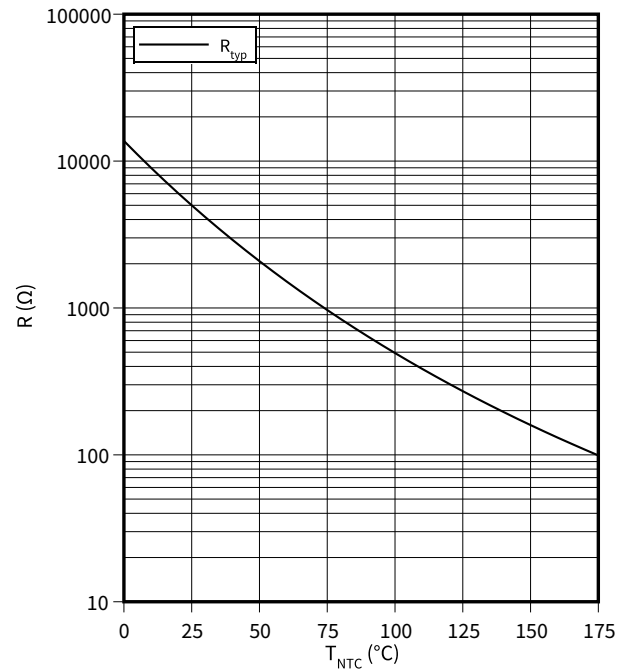
transient thermal impedance , Diode, Inverter

$Z_{th} = f(t)$



temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

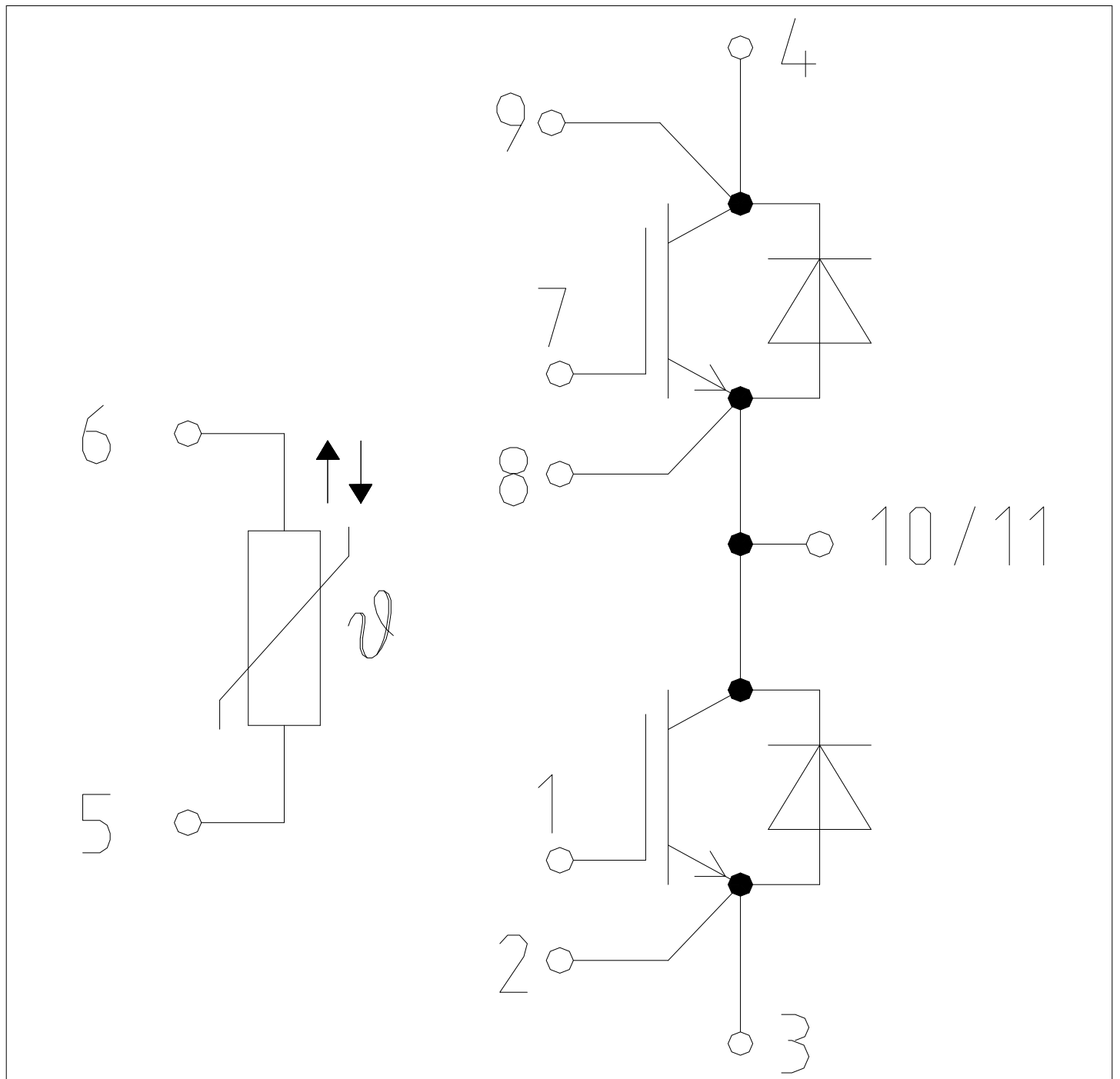


Figure 2

7 Package outlines

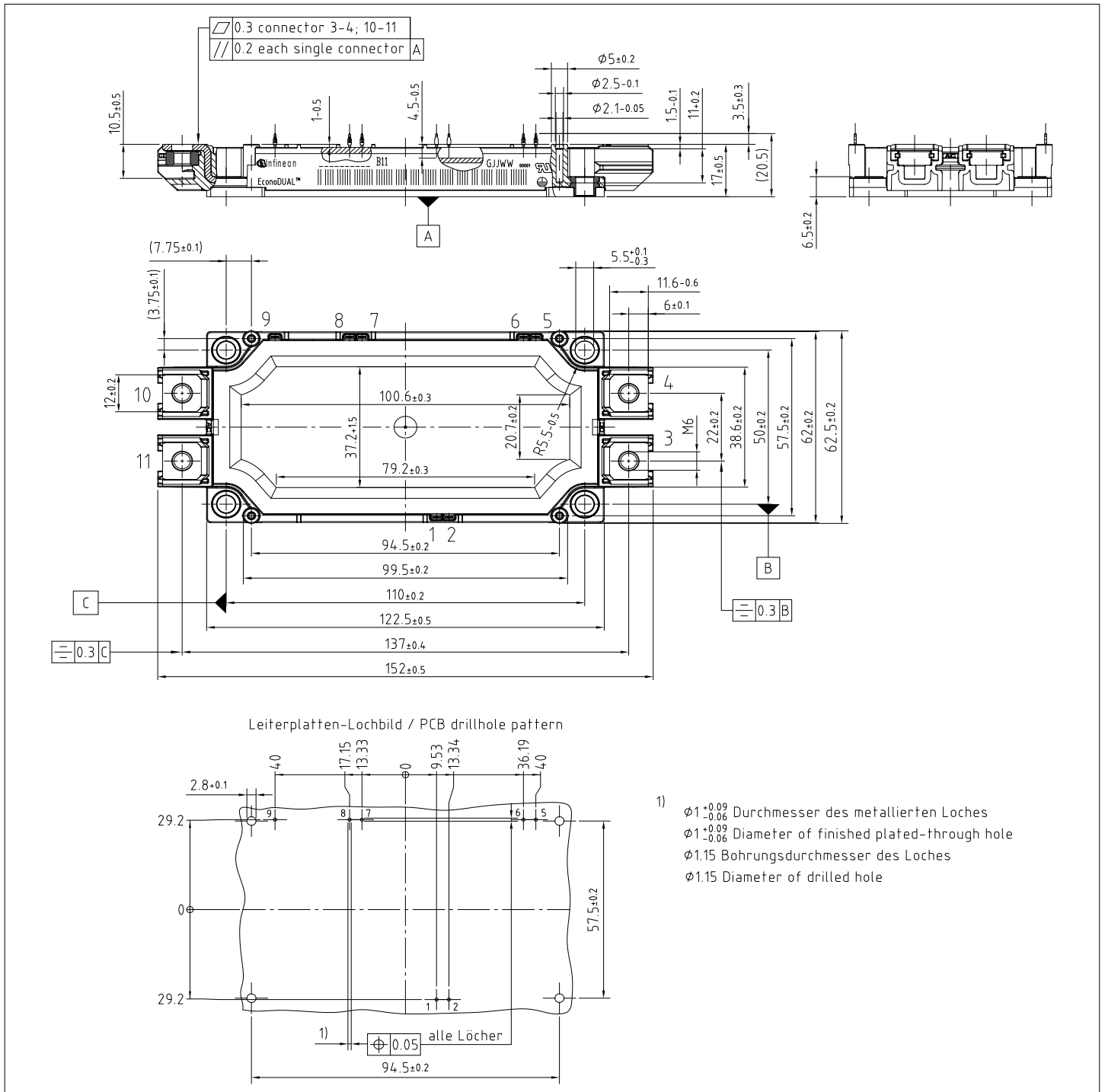


Figure 3

8 Module label code



Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 4

Revision history

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-10-08	Target datasheet
0.10	2020-11-24	Target datasheet
0.11	2021-04-08	Preliminary datasheet
0.12	2021-04-15	Preliminary datasheet
1.00	2021-05-21	Final datasheet

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